

2007/2008/2009

- [1]
O. Bierwagen, L. Geelhaar, X. Gay, M. Piešiņš, H. Riechert, B. Jobst, and A. Rucki, "Leakage currents at crystallites in $ZrAl_xO_y$ thin films measured by conductive atomic-force microscopy," *Applied Physics Letters*, vol. 90, no. 23, pp. 232901–232901–3, Jun. 2007.
- [2]
L. Geelhaar, C. Chèze, W. M. Weber, R. Averbeck, H. Riechert, T. Kehagias, P. Komninou, G. P. Dimitrakopoulos, and T. Karakostas, "Axial and radial growth of Ni-induced GaN nanowires," *Applied Physics Letters*, vol. 91, no. 9, pp. 093113–093113–3, Aug. 2007.
- [3]
W. M. Weber, L. Geelhaar, E. Unger, C. Chèze, F. Kreupl, H. Riechert, and P. Lugli, "Silicon to nickel-silicide axial nanowire heterostructures for high performance electronics," *physica status solidi (b)*, vol. 244, no. 11, pp. 4170–4175, Nov. 2007.
- [4]
Z. Fahem, G. Csaba, C. M. Erlen, P. Lugli, W. M. Weber, L. Geelhaar, and H. Riechert, "Analysis of the hysteretic behavior of silicon nanowire transistors," *physica status solidi (c)*, vol. 5, no. 1, pp. 27–30, Jan. 2008.
- [5]
D. Martin, M. Grube, W. M. Weber, J. Rüstig, O. Bierwagen, L. Geelhaar, and H. Riechert, "Local charge transport in nanoscale amorphous and crystalline regions of high-k $(ZrO_2)_{0.8}(Al_2O_3)_{0.2}$ thin films," *Applied Physics Letters*, vol. 95, no. 14, pp. 142906–142906–3, Oct. 2009.
- [6]